

Silicon NPN Power Transistors

2SD388

DESCRIPTION

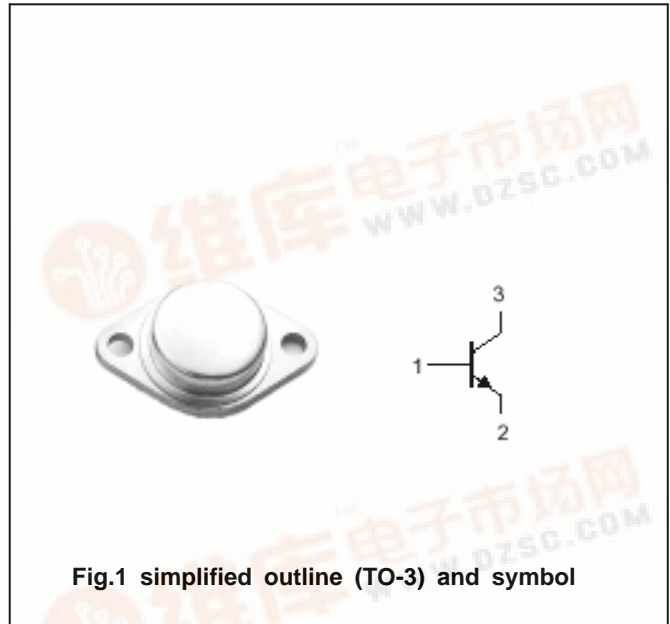
- With TO-3 package
- High power dissipation

APPLICATIONS

- For use in power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	140	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		8	A
P _C	Collector power dissipation	T _C =25	80	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	140			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A ; I _B =0.6A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A ; I _B =0.6A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =150V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	50			
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =5V	20			
f _T	Transition frequency	I _C =1A ; V _{CE} =10V		9		MHz

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PACKAGE OUTLINE

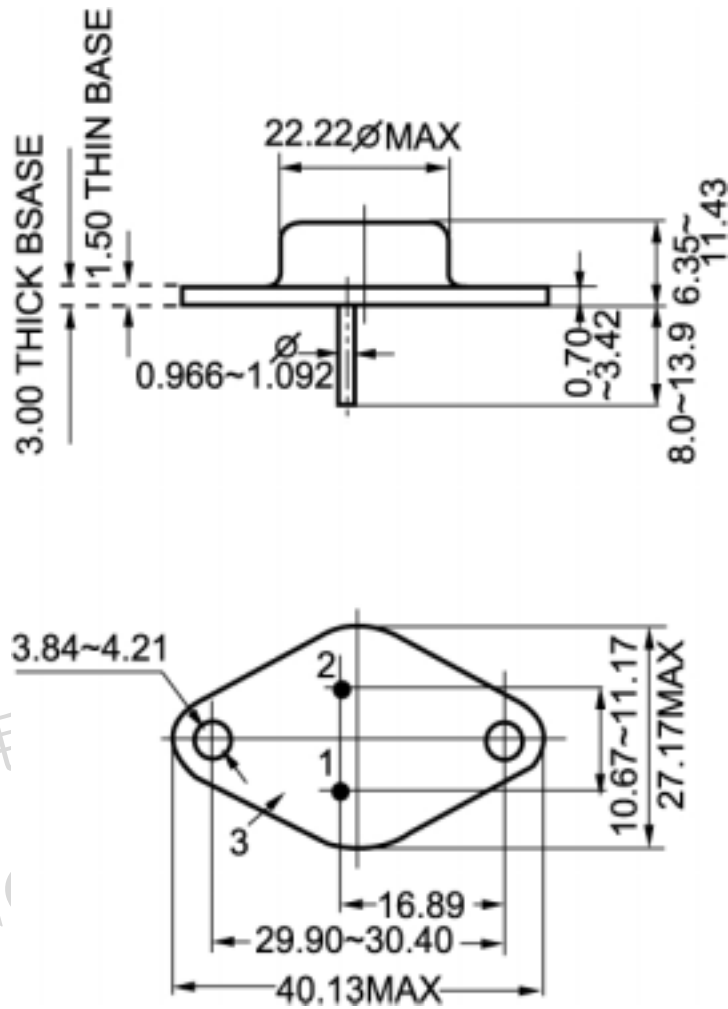


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)